

LISTING OF THE CLAIMS

1. (Previously Presented) A method of forming a layer of a conductive material on a wafer, wherein a seed layer coats a front surface and an edge surface of the wafer, and wherein the edge surface includes a back edge surface, a bevel surface, and a front edge surface, the method comprising:

removing an edge portion of the seed layer from the back edge surface and the bevel surface without removing the seed layer from a central portion of the front surface and front edge surface while the central portion of the seed layer is exposed; and

forming conductive material onto the seed layer coating the front edge surface and the front surface of the wafer after removing the edge portion of the seed layer from the back edge surface and the bevel surface.

2. (Previously Presented) The method of Claim 1, further comprising removing at least a part of the seed layer from the front edge surface.

3. (Previously Presented) The method of Claim 1, further comprising rotating the wafer during removing the edge portion of the seed layer.

4. (Original) The method of Claim 3, further comprising the step of applying a process solution onto the back edge surface of the wafer while it is rotated.

5. (Original) The method of Claim 1, wherein the step of removing comprises chemical etching.

6. (Original) The method of Claim 1, wherein the step of removing comprises electrochemical etching.

7. (Previously Presented) The method of Claim 2, further comprising rotating the wafer prior to removing the at least a part of the seed layer from the front edge surface.

8. (Previously Presented) The method of Claim 7, further comprising applying a process solution to the at least a part of the seed layer on the front edge surface while the wafer is rotated.

9. (Previously Presented) The method of Claim 8, wherein removing the at least a part of the seed layer from the front edge surface comprises chemical etching.

10. (Previously Presented) The method of Claim 8, wherein removing the at least a part of the seed layer from the front edge surface comprises electrochemical etching.

11.-15. (Canceled)

16. (Previously Presented) A method of forming a layer of a conductive material on a wafer comprising a front surface, a back surface and an edge surface, the edge surface including a back edge surface, a bevel surface, and a front edge surface, the method comprising:

depositing a seed layer on the front surface and the edge surface of the wafer;

removing the seed layer from the back edge surface and the bevel surface while the entire seed layer is exposed; and

forming the layer by depositing the conductive material onto the seed layer coating the front edge surface and the front surface after removing the seed layer from the back edge surface and the bevel surface.

17. (Previously Presented) The method of Claim 16, further comprising removing a portion of the seed layer from the front edge surface.

18. (Previously Presented) The method of Claim 16, further comprising rotating the wafer during removing the seed layer from the back edge surface and the bevel surface.

19. (Original) The method of Claim 18, further comprising the step of applying a process solution to the back edge surface while the wafer is rotated.

20. (Original) The method of Claim 16, wherein the step of removing comprises electrochemical removing.

21. (Original) The method of Claim 16, wherein the step of removing comprises chemical removing.

22.-24. (Canceled)

25. (Previously Presented) The method of Claim 2, wherein removing at least part of the seed layer from the front edge surface is conducted after forming the conductive material.

26. (Previously Presented) The method of Claim 17, wherein removing at least part of the seed layer from the front edge surface is conducted after forming the conductive material.

27. (Previously Presented) The method of Claim 1, wherein forming the conductive material includes contacting the seed layer on the front surface or the front edge surface of the wafer.

28. (Previously Presented) The method of Claim 1, wherein removing the edge portion of the seed layer comprises holding the wafer with a wafer carrier and wherein forming the layer comprises holding the wafer with the wafer carrier.

29. (Previously Presented) The method of Claim 5, wherein chemical etching comprises directing an etching solution towards the back edge of the wafer.

30. (Previously Presented) The method of Claim 29, wherein chemical etching comprises rotating the wafer between about 250 and 550 rpm.

31. (Previously Presented) The method of Claim 29, wherein chemical etching comprises rotating the wafer between about 150 and 350 rpm.

32. (Previously Presented) The method of Claim 6, wherein electrochemical etching comprises contacting the wafer with porous media.

33. (Previously Presented) The method of Claim 6, wherein electrochemical etching comprises inserting the edge of the wafer into a cavity.

34. (Previously Presented) The method of Claim 6, wherein electrochemical etching comprises rotating the wafer.